

ABSTRACT OF THE DISCLOSURE

A plurality of grooves having different widths are formed on a surface of an insulating film. Interconnection constituted by a barrier metal and a Cu film is formed in a manner so as to be embedded in the respective grooves. Unevenness formed by, for example, a plurality of grooves are formed on a bottom portion of each of wide grooves having wide widths among the grooves. With this arrangement, it is possible to provide a semiconductor device and a manufacturing method thereof, which can reduce a difference in the deposition rate between the wide grooves and narrow grooves.